Electronic Supplementary Material

Understanding the Spin-Dependent Electronic Properties of Symmetrically Far-Edge Doped Zigzag Graphene Nanoribbon from First Principle Study

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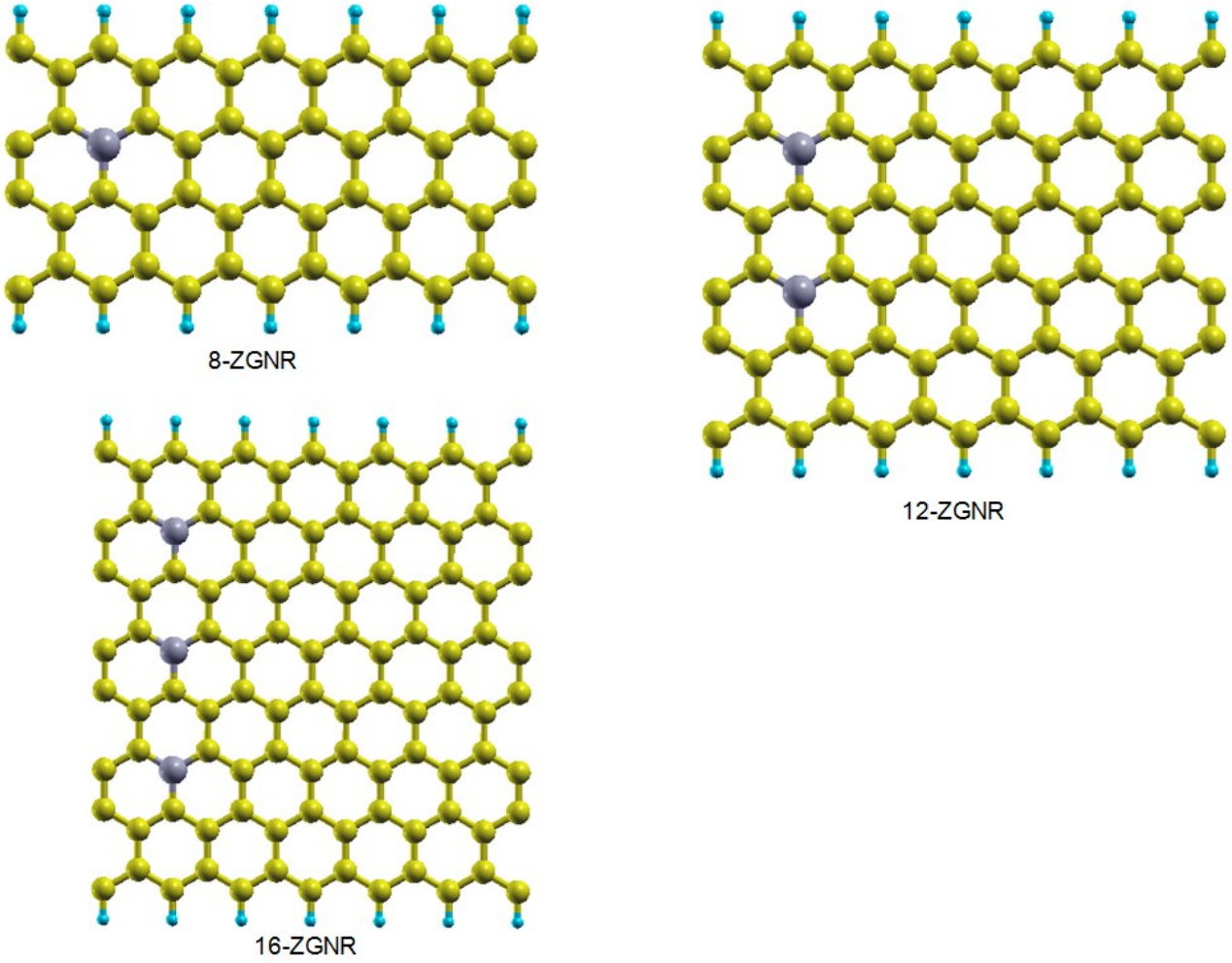

Figure S1: The pictorial representations of the three different zigzag nanoribbon systems considered for our study. Here, the purple colored sites depict the location of doping sites for external impurities i.e., nitrogen and boron.

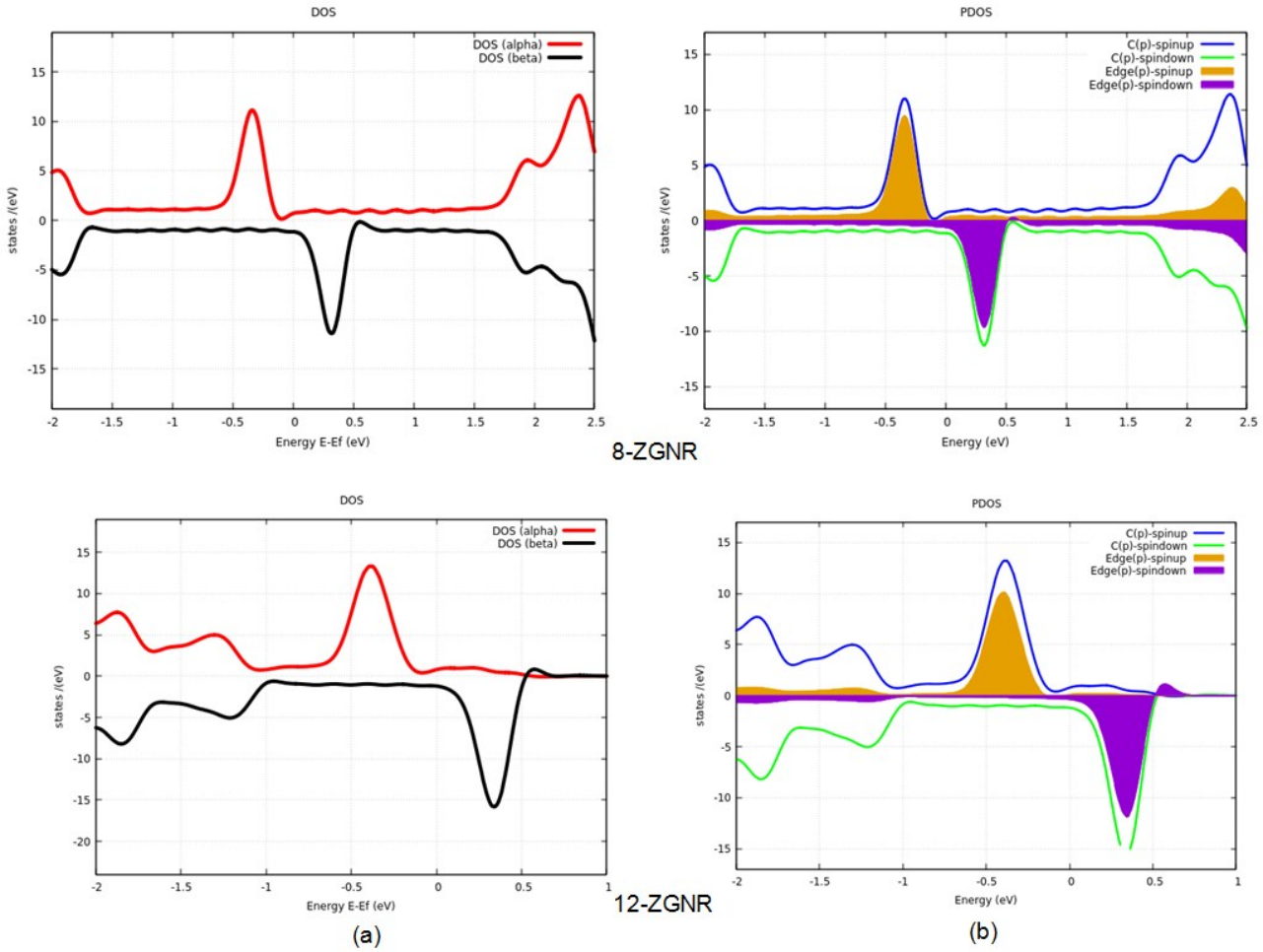

Figure S2: Density of states (DOS) (a, left panel) and projected density of states (PDOS) (b, left panel) for undope 8 and 16-ZGNR systems.

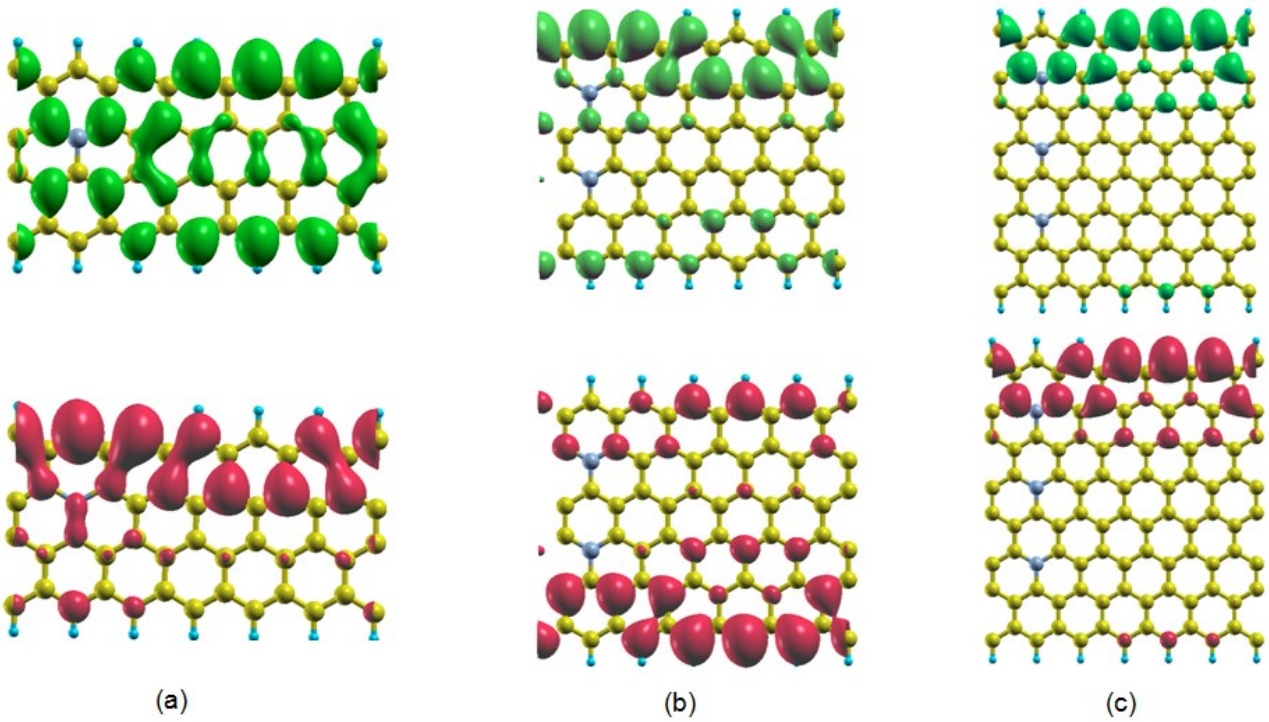

Figure S3: The highest occupied states (lower panel) and lowest unoccupied states (upper panel) for N-doped (a) 8 (b) 12 and (c) 16-ZGNR systems.